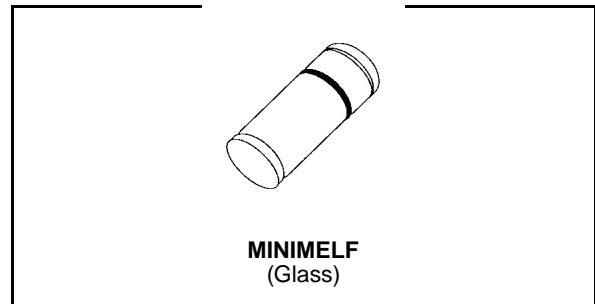


**SMALL SIGNAL SCHOTTKY DIODE****DESCRIPTION**

Metal to silicon junction diode featuring high break-down, low turn-on voltage and ultrafast switching. Primarily intended for high level UHF/VHF detection and pulse application with broad dynamic range.

**ABSOLUTE MAXIMUM RATINGS** (limiting values)

Symbol	Parameter		Value	Unit
$V_{RRM}$	Repetitive Peak Reverse Voltage		60	V
$I_F$	Forward Continuous Current	$T_i = 25^\circ\text{C}$	15	mA
$I_{FSM}$	Surge non Repetitive Forward Current	$t_p \leq 1\text{s}$	50	mA
$T_{stg}$ $T_j$	Storage and Junction Temperature Range		- 65 to 200 -65 to 200	$^\circ\text{C}$
$T_L$	Maximum Temperature for Soldering during 15s		260	$^\circ\text{C}$

**THERMAL RESISTANCE**

Symbol	Test Conditions	Value	Unit
$R_{th(j-l)}$	Junction-leads	400	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS****STATIC CHARACTERISTICS**

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
$V_{BR}$	$T_{amb} = 25^\circ\text{C}$	$I_R = 10\mu\text{A}$	60			V
$V_F^*$	$T_{amb} = 25^\circ\text{C}$	$I_F = 1\text{mA}$			0.41	V
	$T_{amb} = 25^\circ\text{C}$	$I_F = 15\text{mA}$			1	
$I_R^*$	$T_{amb} = 25^\circ\text{C}$	$V_R = 50\text{V}$			0.2	$\mu\text{A}$

**DYNAMIC CHARACTERISTICS**

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
C	$T_{amb} = 25^\circ\text{C}$	$V_R = 0\text{V}$	$f = 1\text{MHz}$			2.2	pF
$\tau$	$T_{amb} = 25^\circ\text{C}$	$I_F = 5\text{mA}$	Krakauer Method			100	ps

\* Pulse test:  $t_p \leq 300\mu\text{s}$   $\delta < 2\%$ .

Matched batches available on request. Test conditions (forward voltage and/or capacitance) according to customer specification.

Figure 1. Forward current versus forward voltage (typical values).

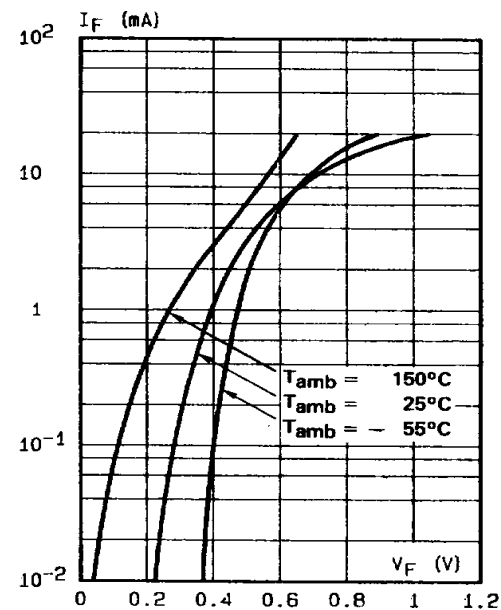


Figure 2. Capacitance C versus reverse applied voltage  $V_R$  (typical values).

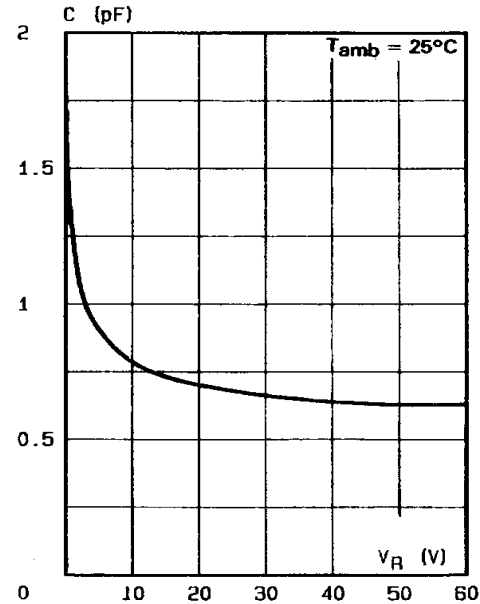


Figure 3. Reverse current versus ambient temperature.

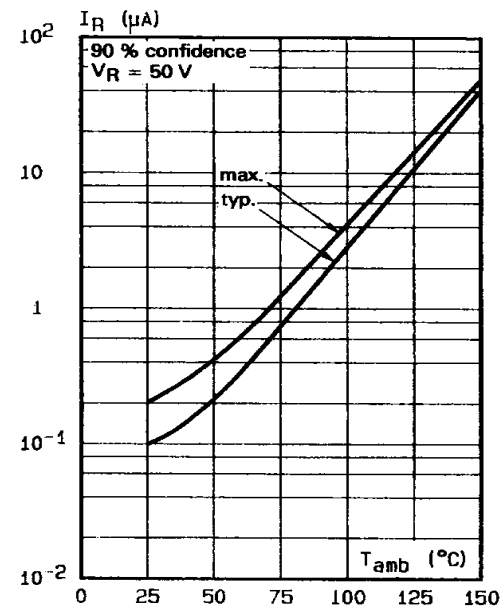
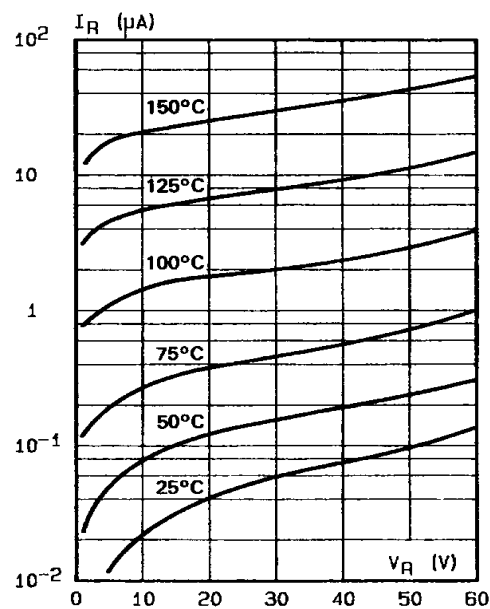
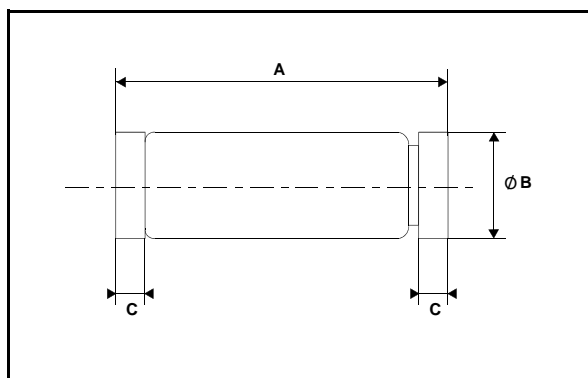


Figure 4. Reverse current versus continuous reverse voltage (typical values).



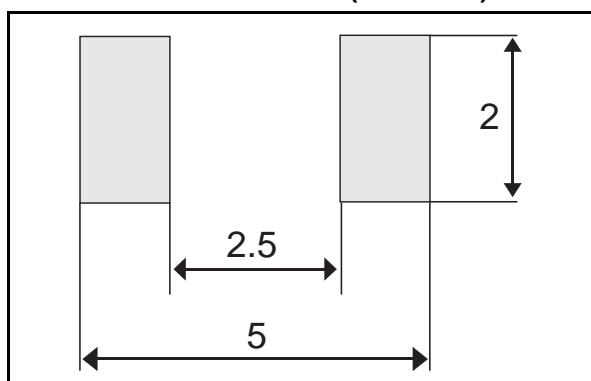
## PACKAGE MECHANICAL DATA

## MINIMELF Glass



REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	3.30	3.40	3.6	0.130	0.134	0.142
B	1.59	1.60	1.62	0.063	0.063	0.064
C	0.40	0.45	0.50	0.016	0.018	0.020
D		1.50			0.059	

## FOOT PRINT DIMENSIONS (Millimeter)



Marking: ring at cathode end.  
Weight: 0.05g

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